

IN THE CLAIMS:

Please amend the claims as follows:

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3. (Amended) A semiconductor device comprising:
- a substrate having an insulating surface;
  - a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; and insulating layer formed on the gate electrode; a channel formation region formed in a semiconductor layer having an amorphous structure; source and drain regions, each of the source and drain regions comprising a semiconductor layer including one-conductive type impurity elements, formed over the semiconductor layer having the amorphous structure;
  - an interlayer insulating layer comprising an inorganic material and formed on the semiconductor layer having the amorphous structure and the semiconductor layer containing the one-conductive type impurity elements so as to be in contact with at least a part of the channel formation region;
  - a pixel electrode formed in contact with the insulating layer; and
  - an input terminal portion formed along an end portion of the substrate and electrically connected to a wiring of another substrate;
- wherein the input terminal portion includes a first layer comprising the same material as that of the gate electrode and a second layer comprising the same material as that of the pixel electrode.

REMARKS

It is not believed that any further fee should be due for this amendment. If any further fee is due, please charge our Deposit Account No. 50-1039.